M1MA151WKT1, M1MA152WKT1

Preferred Device

Common Cathode Silicon Dual Switching Diodes

These Common Cathode Silicon Epitaxial Planar Dual Diodes are designed for use in ultra high speed switching applications. These devices are housed in the SC–59 package which is designed for low power surface mount applications.

Features

- Fast t_{rr} , < 3.0 ns
- Low C_D, < 2.0 pF
- Pb–Free Packages are Available

MAXIMUM RATINGS ($T_A = 25^{\circ}C$)

Rating		Symbol	Value	Unit
Reverse Voltage M1MA15 M1MA15		V _R	40 80	Vdc
Peak Reverse Voltage M1MA15 M1MA15		V _{RM}	40 80	Vdc
Forward Current	Single Dual	Ι _F	100 150	mAdc
Peak Forward Current	Single Dual	I _{FM}	225 340	mAdc
Peak Forward Surge Current	Single Dual	I _{FSM} (Note 1)	500 750	mAdc

THERMAL CHARACTERISTICS

Rating	Symbol	Max	Unit
Power Dissipation	PD	200	mW
Junction Temperature	TJ	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

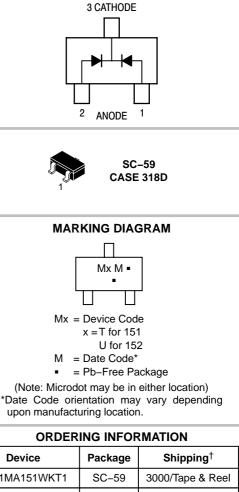
1. t = 1 SEC



ON Semiconductor®

http://onsemi.com

SC-59 PACKAGE SINGLE SILICON SWITCHING DIODES 40 V/80 V 100 mA SURFACE MOUNT



Device	Package	Shipping [†]	
M1MA151WKT1	SC-59	3000/Tape & Reel	
M1MA151WKT1G	SC-59 (Pb-Free)	3000/Tape & Reel	
M1MA152WKT1	SC-59	3000/Tape & Reel	
M1MA152WKT1G	SC–59 (Pb–Free)	3000/Tape & Reel	

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

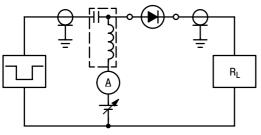
M1MA151WKT1, M1MA152WKT1

ELECTRICAL CHARACTERISTICS (T_A = 25° C)

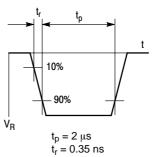
Characteristic		Symbol	Condition	Min	Max	Unit μAdc
Reverse Voltage Leakage Current	M1MA151WKT1 M1MA152WKT1	Ι _R	V _R = 35 V V _R = 75 V			
Forward Voltage		V _F	l _F = 100 mA	-	1.2	Vdc
Reverse Breakdown Voltage	M1MA151WKT1 M1MA152WKT1	V _R	I _R = 100 μA	40 80	-	Vdc
Diode Capacitance		CD	V _R = 0, f = 1.0 MHz	-	2.0	pF
Reverse Recovery Time (Figure 1)		t _{rr} (Note 2)	$I_{F} = 10 \text{ mA}, V_{R} = 6.0 \text{ V}, R_{L} = 100 \Omega, I_{rr} = 0.1 I_{R}$	-	3.0	ns

2. t_{rr} Test Circuit

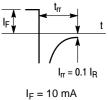












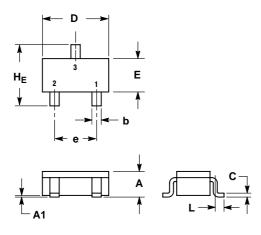
 $V_{\rm R} = 6 V$ $R_{\rm L} = 100 \Omega$



M1MA151WKT1, M1MA152WKT1

PACKAGE DIMENSIONS

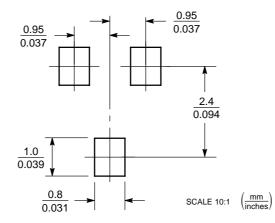
SC-59 CASE 318D-04 ISSUE G



NOTES 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982. 2. CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS			INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	1.00	1.15	1.30	0.039	0.045	0.051	
A1	0.01	0.06	0.10	0.001	0.002	0.004	
b	0.35	0.43	0.50	0.014	0.017	0.020	
С	0.09	0.14	0.18	0.003	0.005	0.007	
D	2.70	2.90	3.10	0.106	0.114	0.122	
Е	1.30	1.50	1.70	0.051	0.059	0.067	
е	1.70	1.90	2.10	0.067	0.075	0.083	
L	0.20	0.40	0.60	0.008	0.016	0.024	
ΗE	2.50	2.80	3.00	0.099	0.110	0.118	

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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